

High-performance transparent inorganic–organic hybrid thin-film n-type transistors

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The above article contained two typographical errors:

1. In the caption for Figure 4c,d, the TFT device source–drain length should have read 50 μm (L).
2. In Methods, in the equation in the Characterization Methodology section, the parameter N_i should have been squared, that is:

$$I_{\text{DS}} = \frac{W\mu_{\text{GB}}V_{\text{D}}C_{\text{i}}V_{\text{G}}}{L} \exp\left(\frac{-q^3N_{\text{i}}^2t}{8\epsilon kTC_{\text{i}}V_{\text{G}}}\right)$$

The erroneous length and equation were not used in deriving any of the reported physical parameters, and the scientific conclusions of the paper remain unchanged.